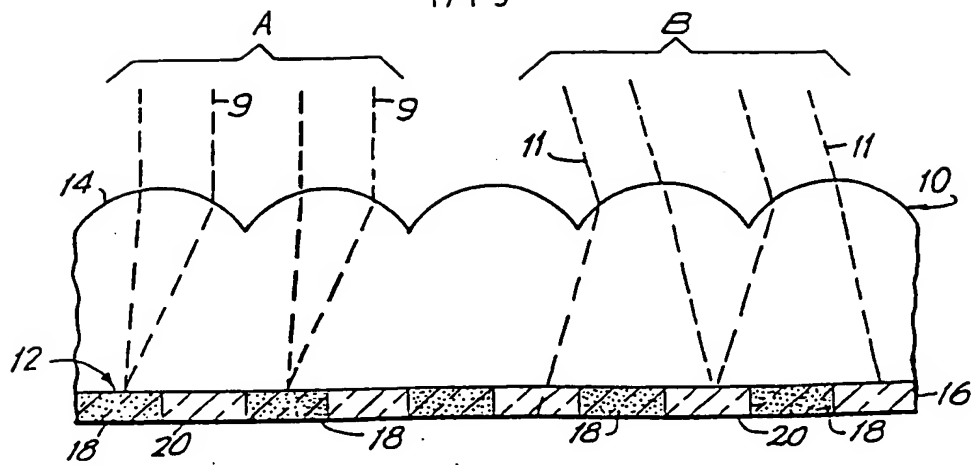
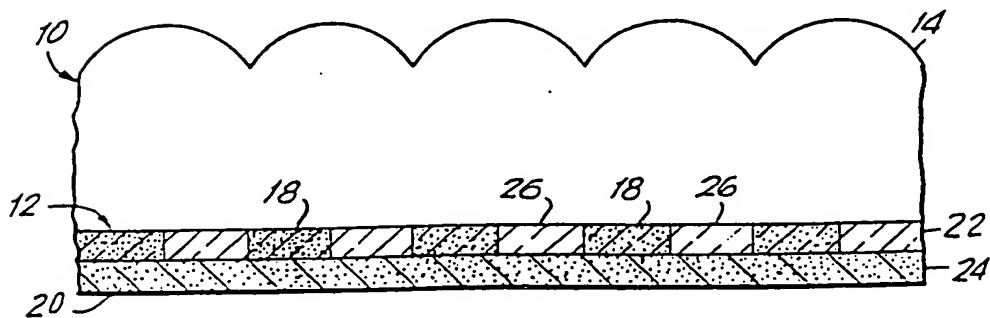


FIG. 1

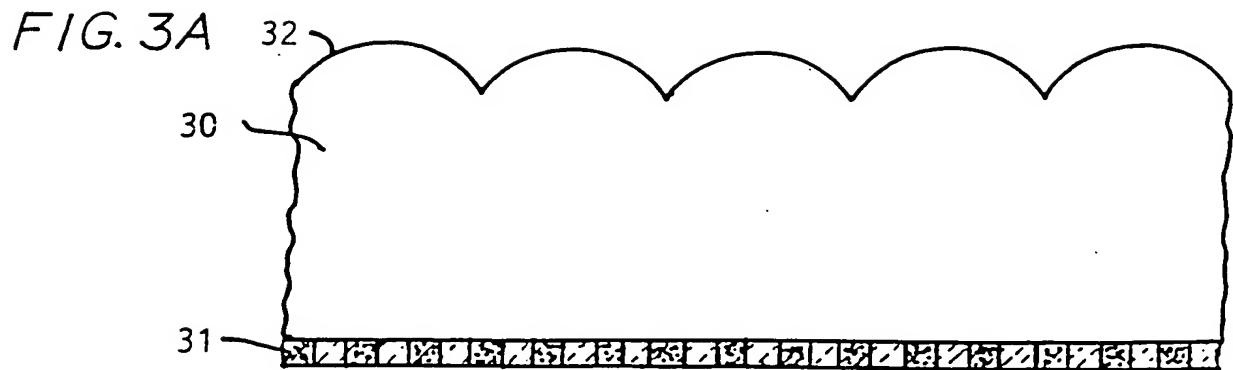


PRIOR ART

FIG. 2



PRIOR ART



PRIOR ART

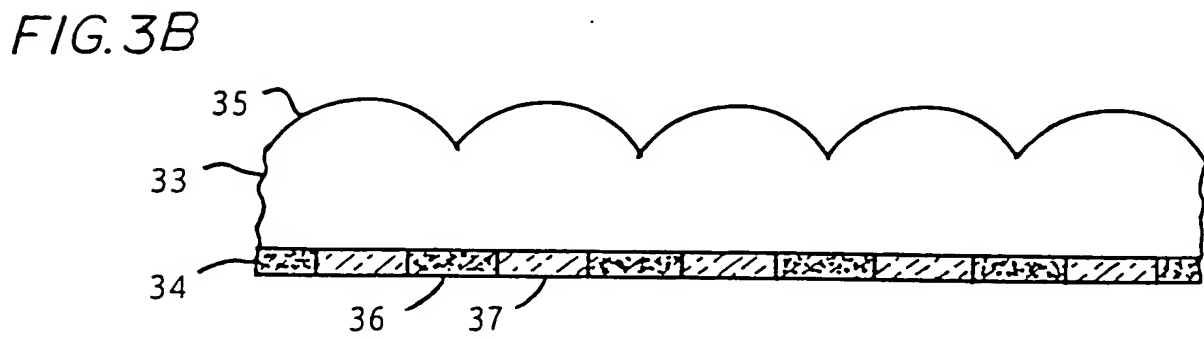


FIG. 4

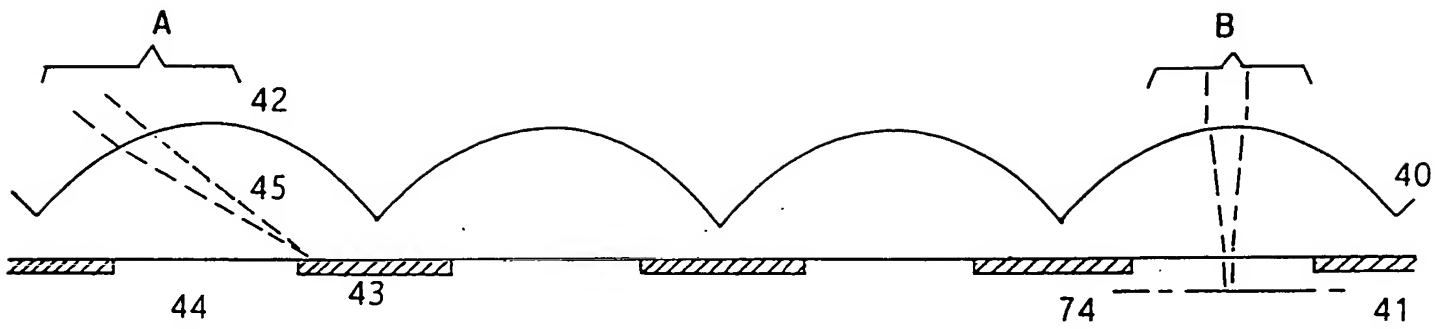


FIG. 5

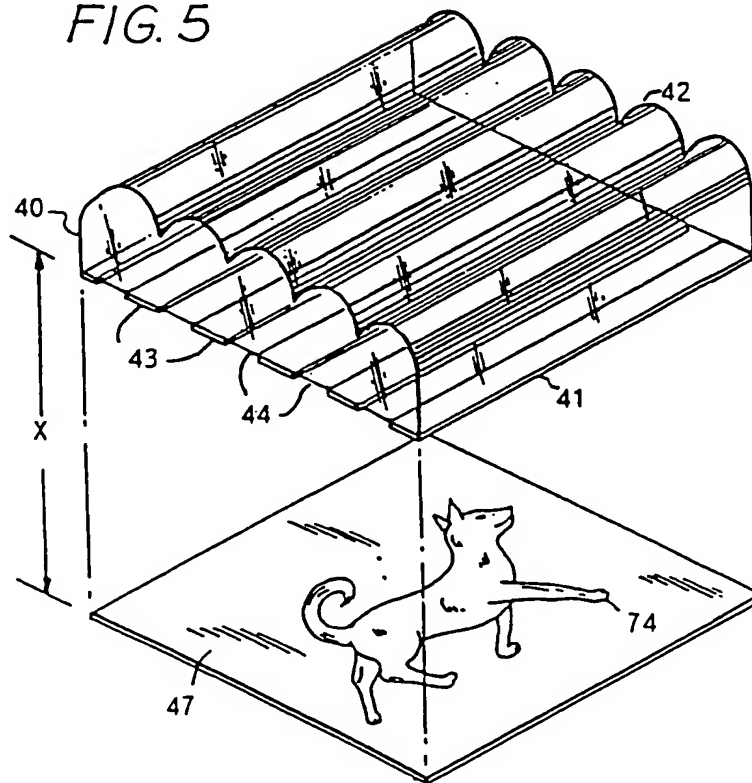


FIG. 6

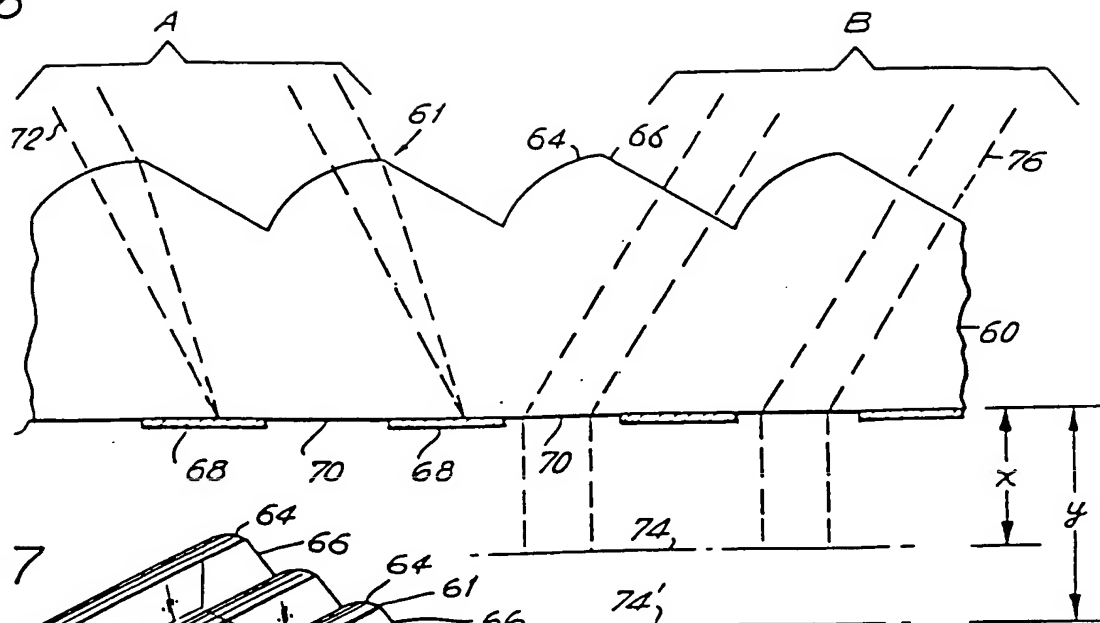
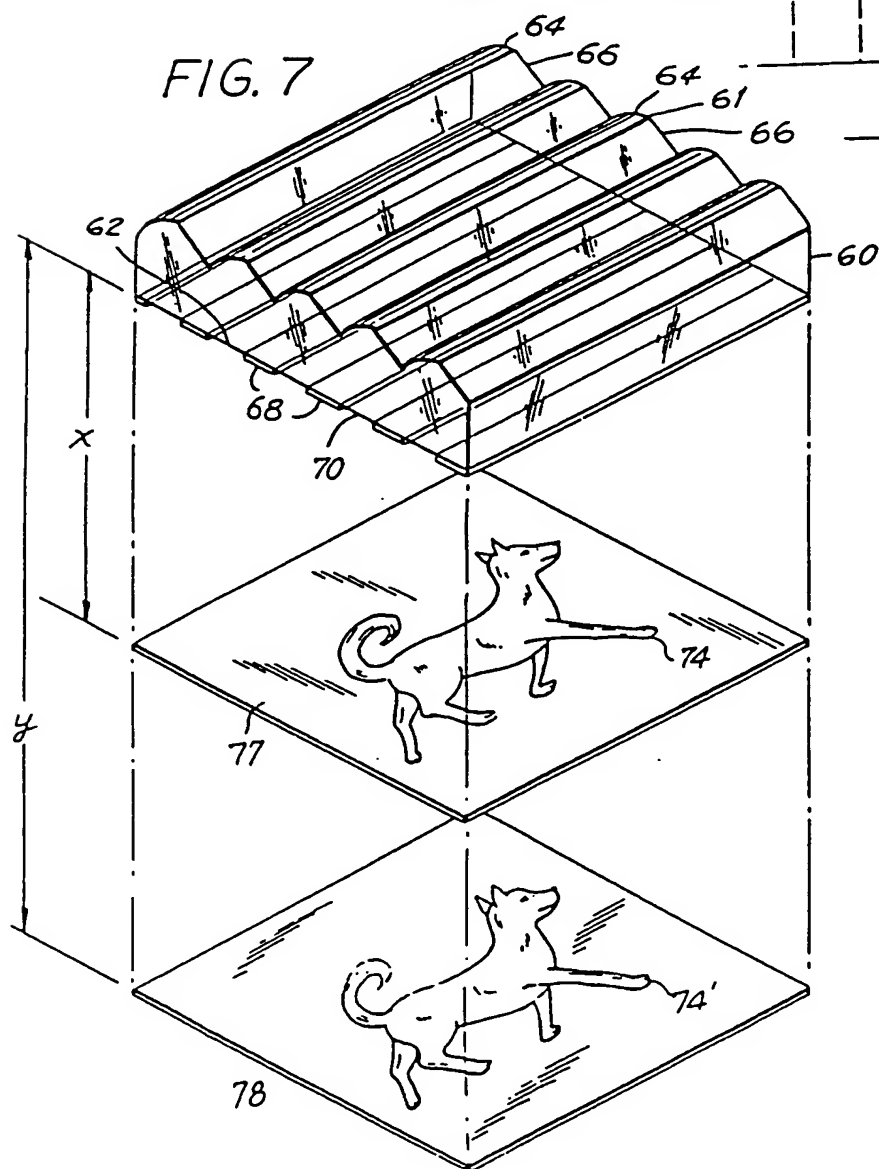
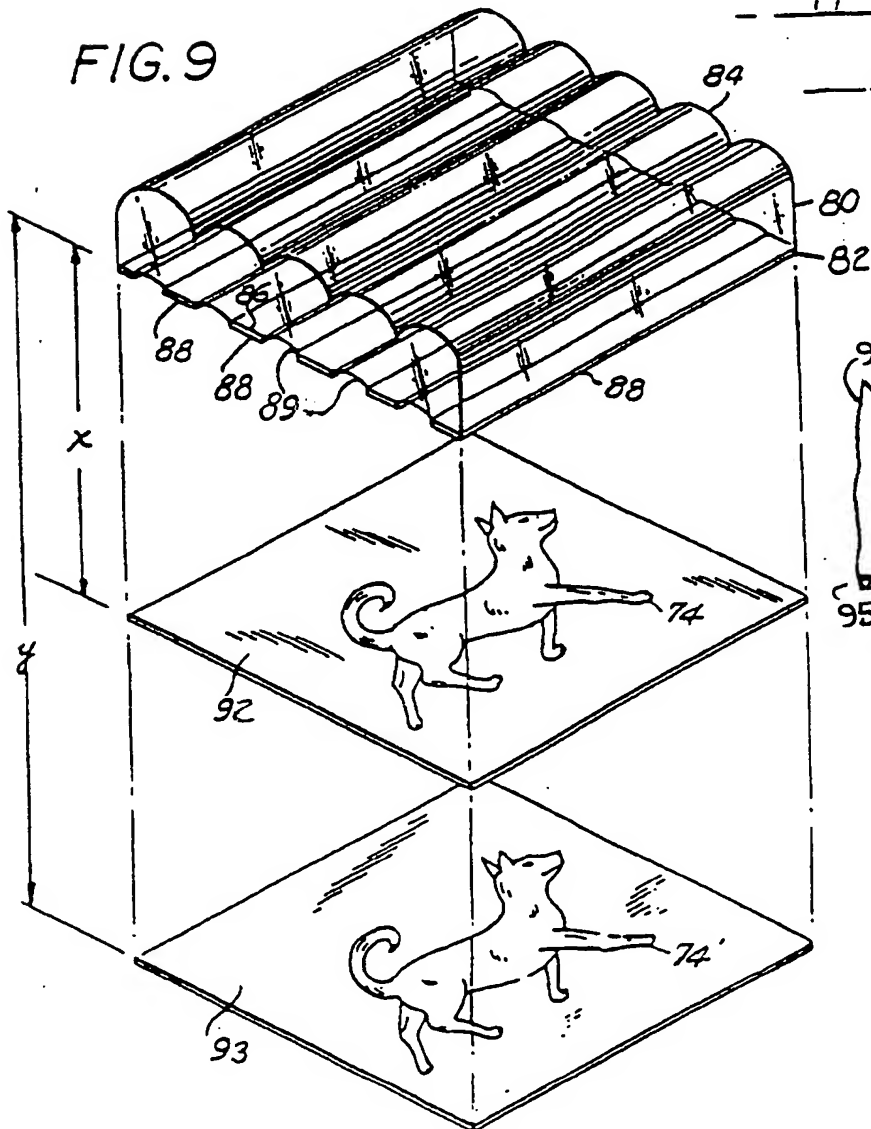
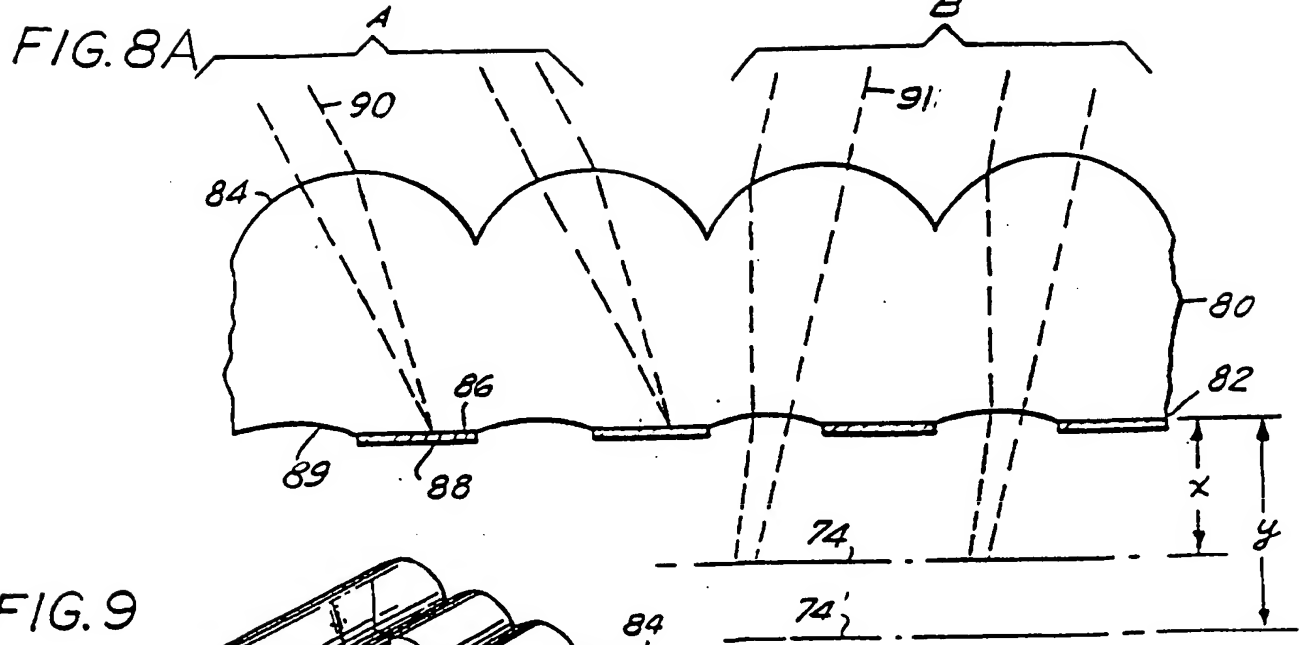


FIG. 7





A cross-sectional view of a semiconductor device. A substrate 74 is shown at the bottom. On the substrate, there are several rectangular regions 102, 110, 108, and 106, which are shaded with diagonal lines. Above these regions, a series of curved, wave-like structures 100 are formed. The top surface of the device is labeled 101. A dashed line 104 indicates a cross-section through the device. A bracket 112 is shown above the first wave. A bracket 114 is shown above the last wave. A point X is marked on the substrate 74.

FIG. 12

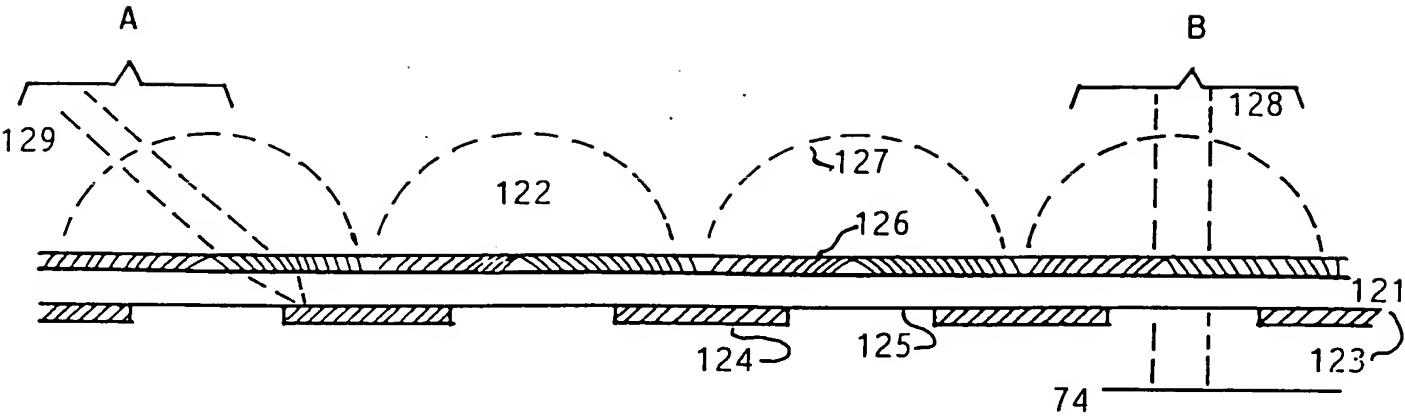


FIG. 13

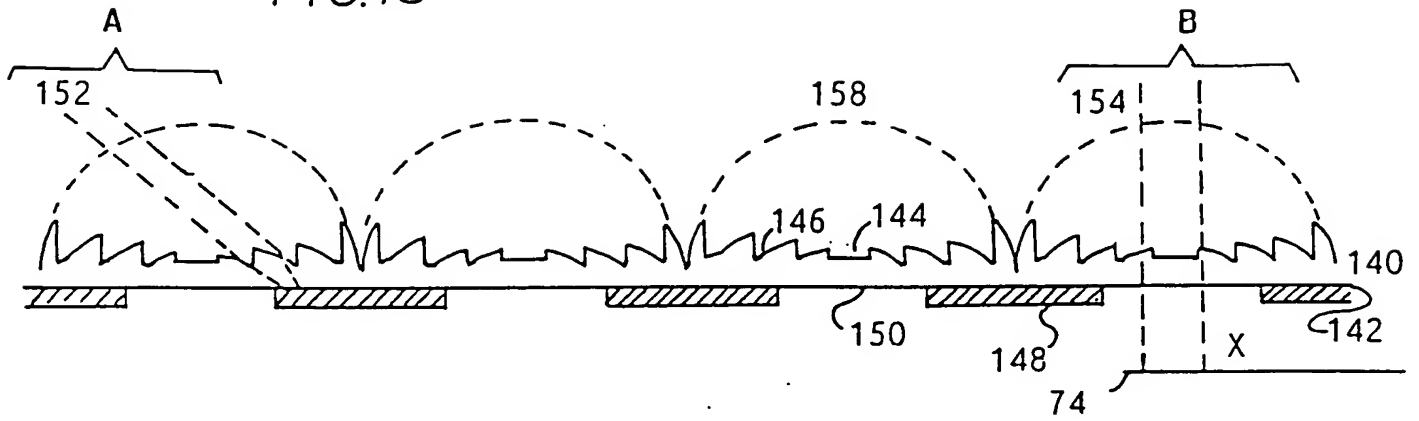


FIG. 14

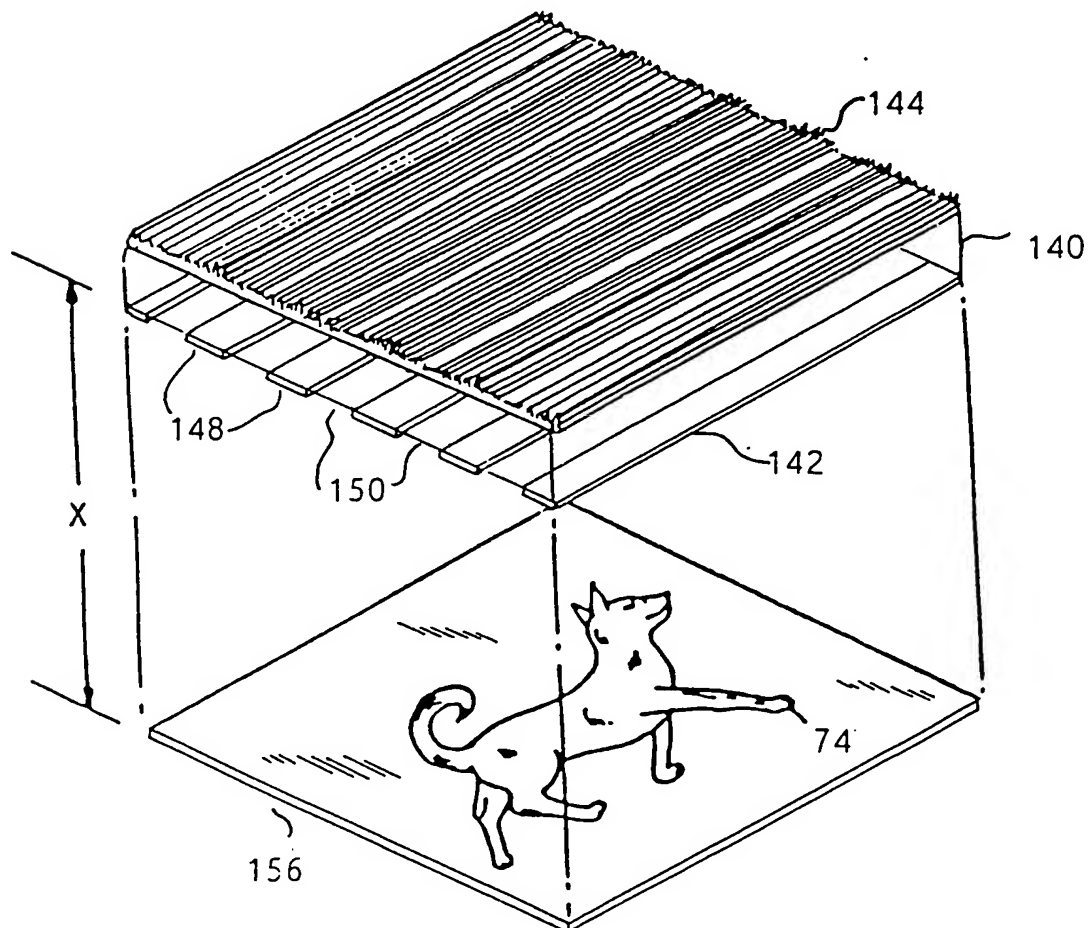




FIG. 15

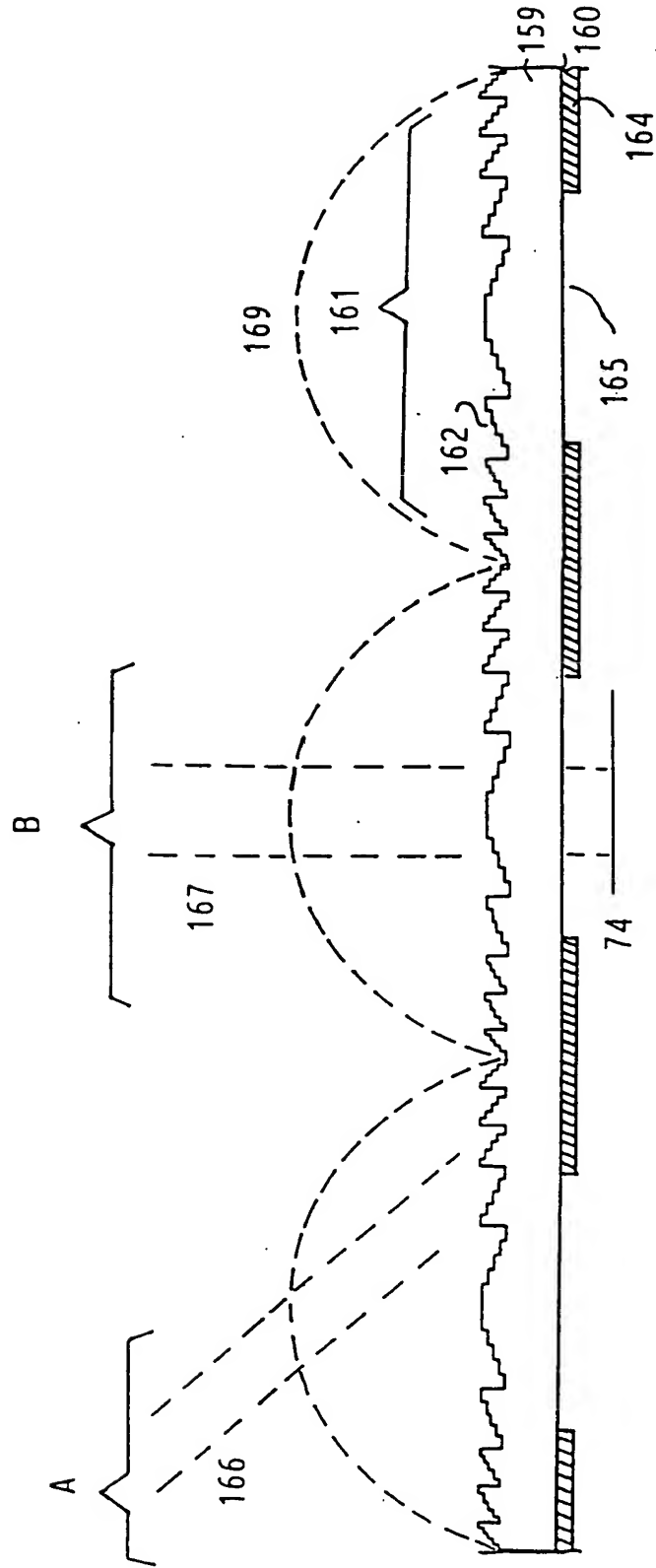


FIG. 16

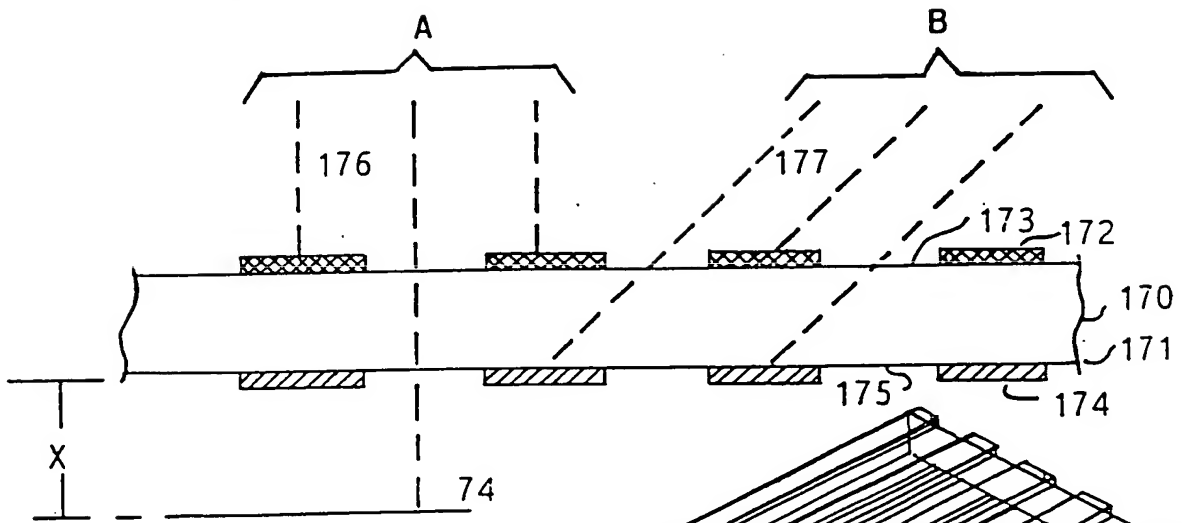


FIG. 17

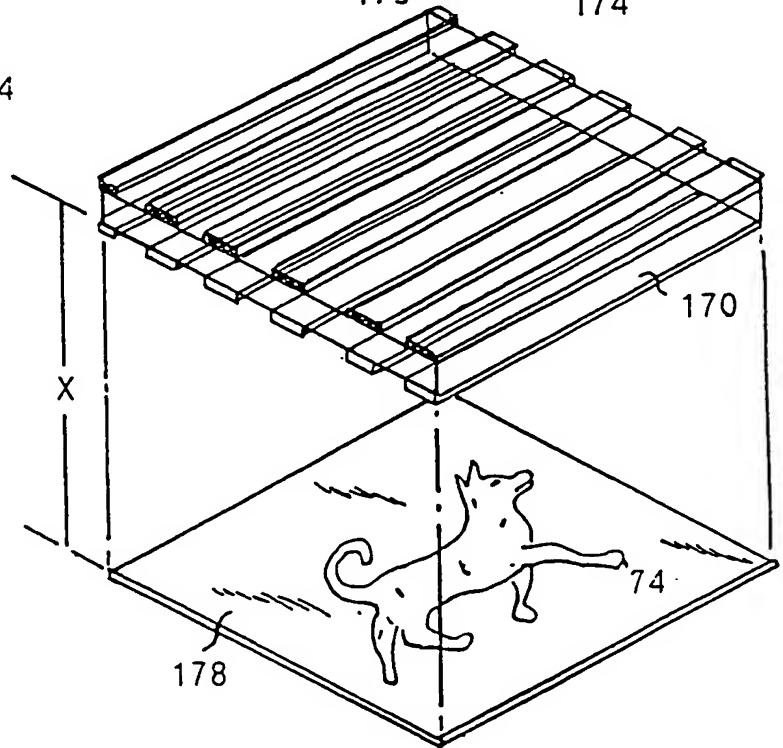


FIG. 18A

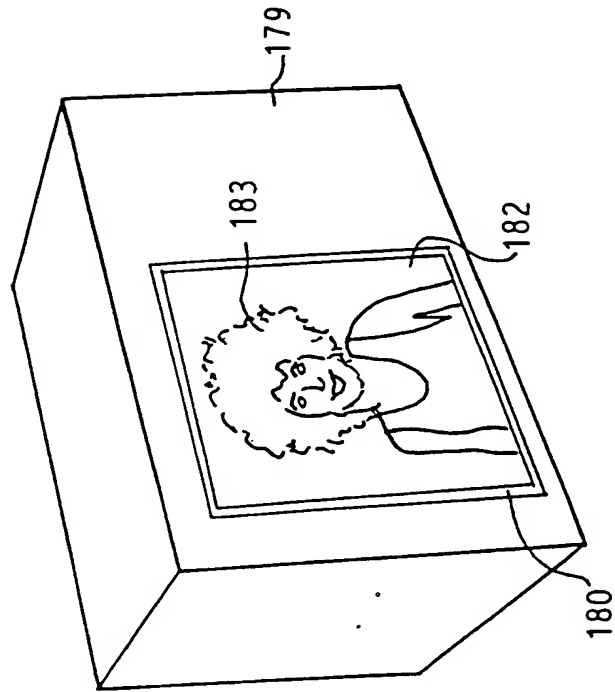


FIG. 18B

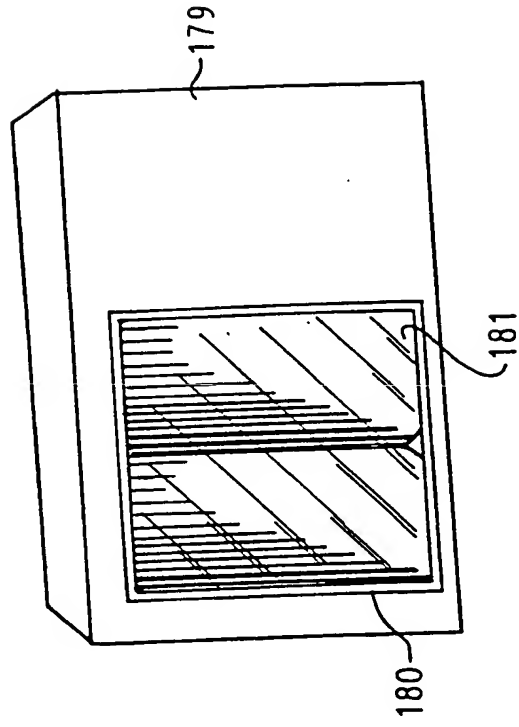


FIG. 19A

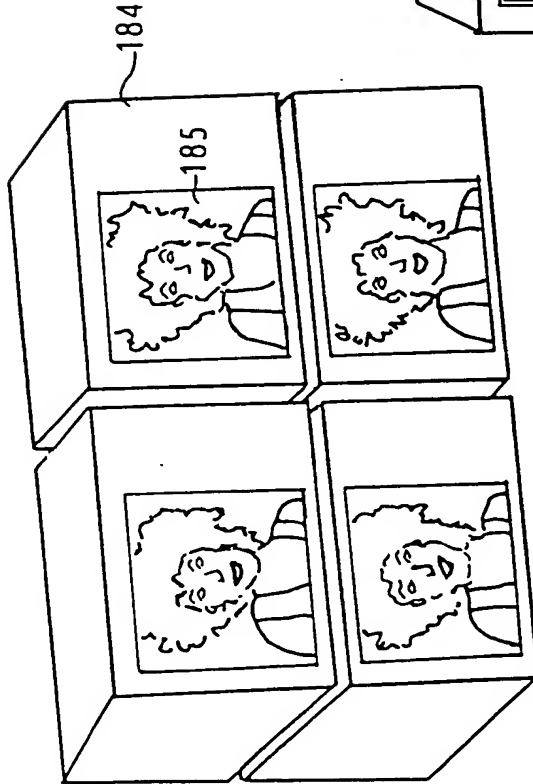


FIG. 19B

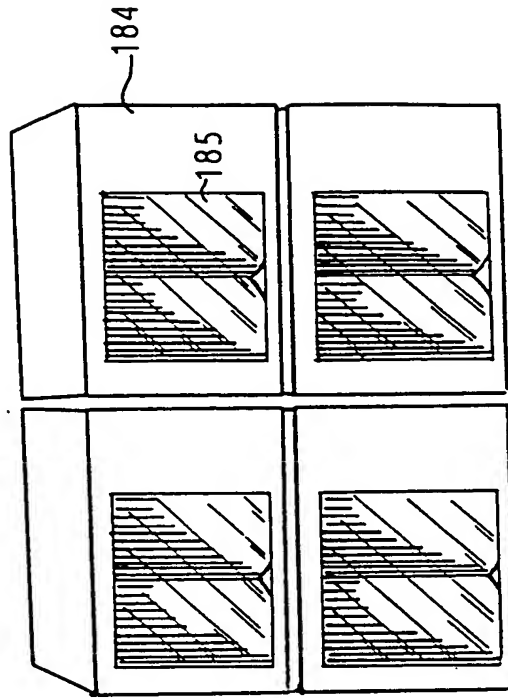


FIG. 20A

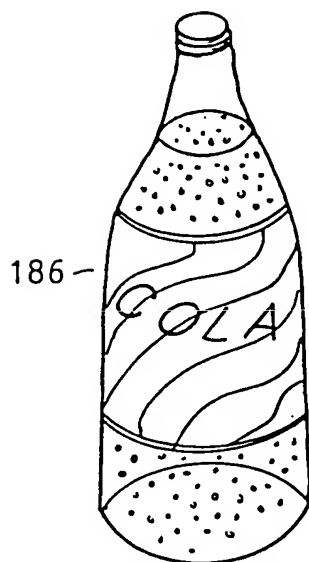


FIG 20B

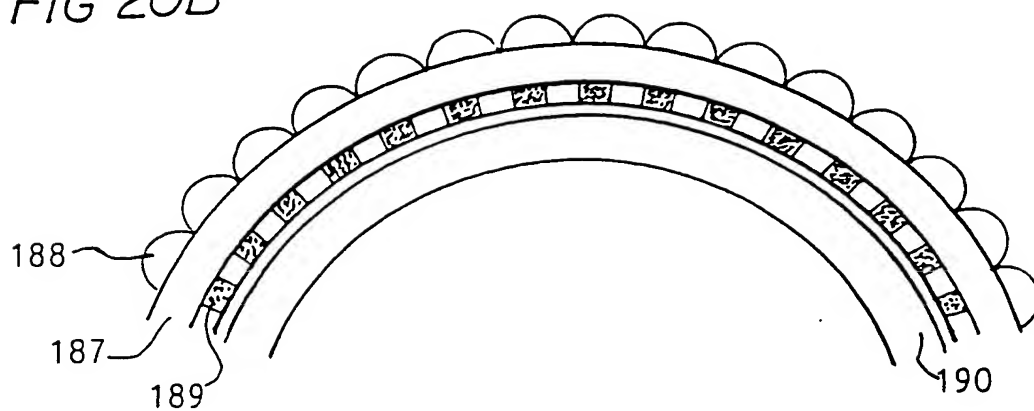


FIG. 21

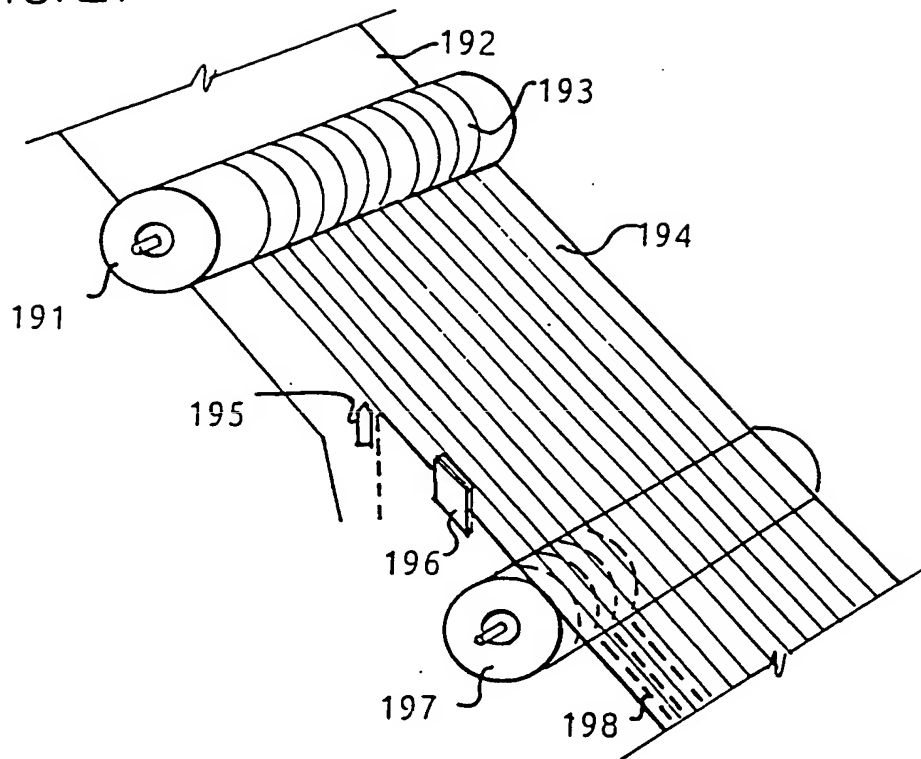
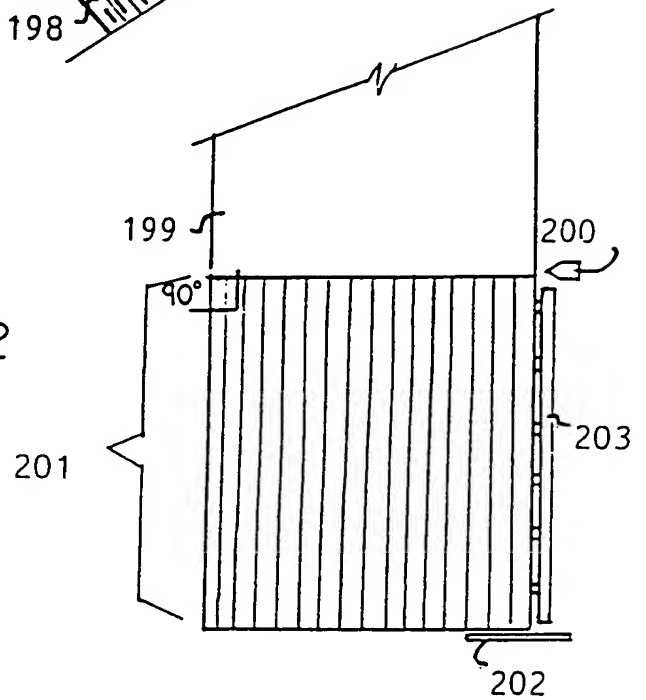
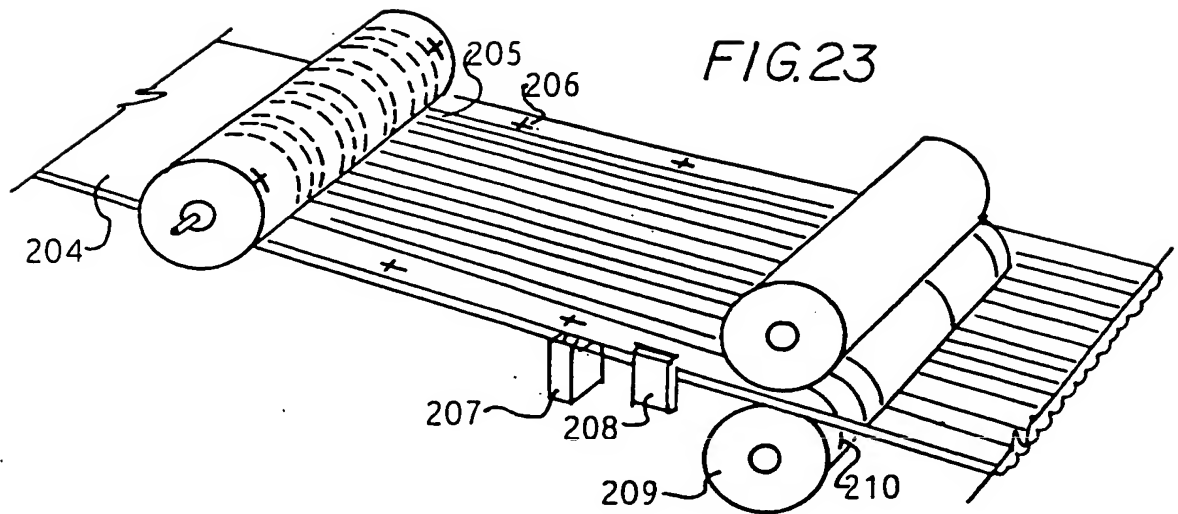
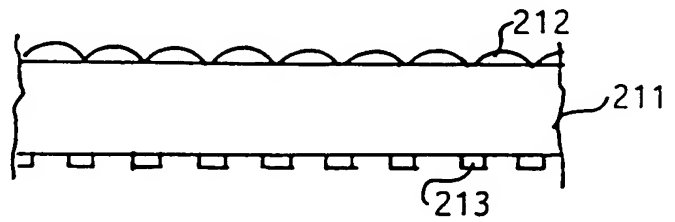


FIG. 22

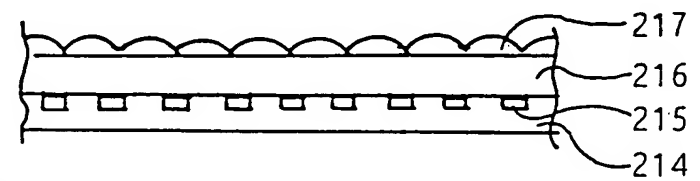




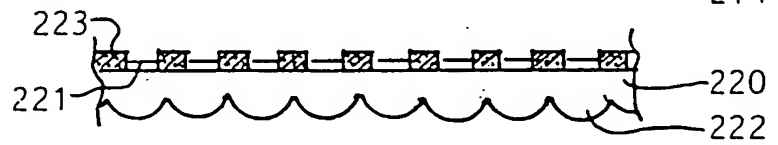
*FIG. 24*



*FIG. 25*



*FIG. 26*



*FIG. 27*

